Silicon NPN Planar RF Transistor

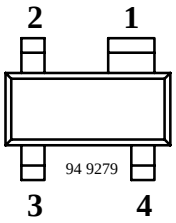
Electrostatic sensitive device.
Observe precautions for handling.

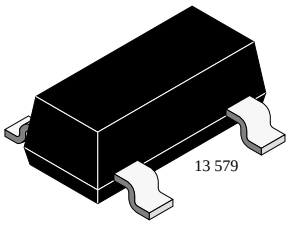
Applications

Low noise small signal amplifiers up to 2 GHz. This transistor has superior noise figure and associated gain performance at UHF, VHF and microwave frequencies.

Features

- Small feedback capacitance
- Low noise figure
- High transition frequency





BFG67 Marking: V3
Plastic case (SOT 143)
1 = Collector, 2 = Base, 3 = Emitter, 4 = Emitter

Absolute Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Collector-base voltage		V_{CBO}	20	V
Collector-emitter voltage		V_{CEO}	10	V
Emitter-base voltage		V_{EBO}	2.5	V
Collector current		I_C	50	mA
Total power dissipation	$T_{amb} \leq 60$ °C	P_{tot}	200	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	–65 to +150	°C

Maximum Thermal Resistance

T_{amb} = 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on glass fibre printed board (25 x 20 x 1.5) mm^3 plated with 35µm Cu	R_{thJA}	450	K/W

Electrical DC Characteristics

T_{amb} = 25°C, unless otherwise specified

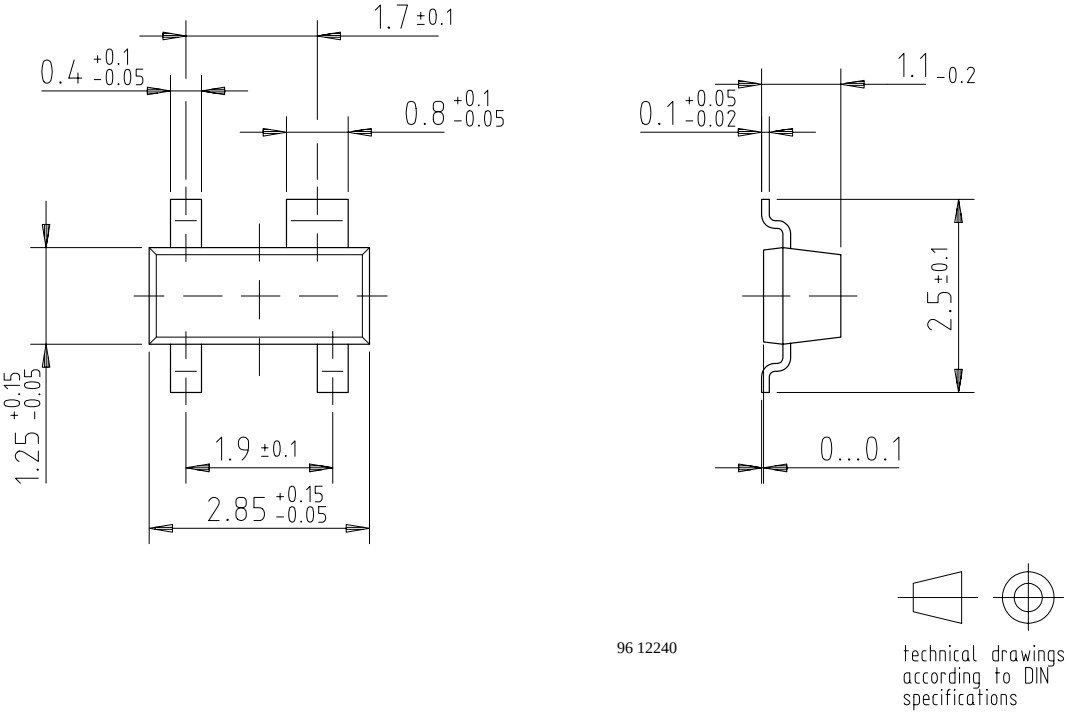
Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Collector cut-off current	V_{CE} = 20 V, V_{BE} = 0	I_{CES}			100	µA
Collector-base cut-off current	V_{CB} = 15 V, I_E = 0	I_{CBO}			100	nA
Emitter-base cut-off current	V_{EB} = 1 V, I_C = 0	I_{EBO}			1	µA
Collector-emitter breakdown voltage	I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	10			V
Collector-emitter saturation voltage	I_C = 50 mA, I_B = 5 mA	V_{CEsat}		0.1	0.4	V
DC forward current transfer ratio	V_{CE} = 5 V, I_C = 15 mA	h_{FE}	65	100	150	

Electrical AC Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Transition frequency	V_{CE} = 8 V, I_C = 15 mA, f = 500 MHz	f_T		7.5		GHz
Collector-base capacitance	V_{CB} = 10 V, f = 1 MHz	C_{cb}		0.35		pF
Collector-emitter capacitance	V_{CE} = 8 V, f = 1 MHz	C_{ce}		0.25		pF
Emitter-base capacitance	V_{EB} = 0.5 V, f = 1 MHz	C_{eb}		0.85		pF
Noise figure	V_{CE} = 8 V, Z_S = Z_{Sopt}, f = 800 MHz, I_C = 5 mA	F		0.8		dB
	V_{CE} = 8 V, Z_S = Z_{Sopt}, f = 800 MHz, I_C = 15 mA	F		1.5		dB
	V_{CE} = 8 V, Z_S = 50 Ω, f = 2 GHz, I_C = 5 mA	F		2.5		dB
	V_{CE} = 8 V, Z_S = 50 Ω, f = 2 GHz, I_C = 15 mA	F		3.0		dB
Power gain	V_{CE} = 8 V, Z_S = 50 Ω, Z_L = Z_{Lopt}, I_C = 15 mA, f = 800 MHz	G_{pe}		17		dB
	V_{CE} = 8 V, Z_S = 50 Ω, Z_L = Z_{Lopt}, I_C = 15 mA, f = 2 GHz	G_{pe}		9		dB
Linear output voltage – two tone intermodulation test	V_{CE} = 8 V, I_C = 15 mA, d_{IM} = 60 dB, f_1 = 806 MHz, f_2 = 810 MHz, Z_S = Z_L = 50 Ω	$V_1 = V_2$		160		mV
Third order intercept point	V_{CE} = 8 V, I_C = 15 mA, f = 800 MHz	IP_3		26		dBm

Dimensions of BFG67 in mm



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.

2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively

2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA

3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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